

Andreas Waag

List of Publications by Year in descending order

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164
papers

3,555
citations

159585

30
h-index

168389

53
g-index

169
all docs

169
docs citations

169
times ranked

3541
citing authors

#	ARTICLE	IF	CITATIONS
1	Visible-Light-Driven Room Temperature NO ₂ Gas Sensor Based on Localized Surface Plasmon Resonance: The Case of Gold Nanoparticle Decorated Zinc Oxide Nanorods (ZnO NRs). <i>Chemosensors</i> , 2022, 10, 28.	3.6	8
2	Gradients in Three-Dimensional Core-Shell GaN/InGaN Structures: Optimization and Physical Limitations. <i>ACS Applied Materials & Interfaces</i> , 2022, 14, 9272-9280.	8.0	5
3	AlGaIn Microfins as Nonpolar UV Emitters Probed by Time-Resolved Cathodoluminescence. <i>ACS Photonics</i> , 2022, 9, 1594-1604.	6.6	5
4	Ultrashort Pulse Laser Lift-Off Processing of InGaN/GaN Light-Emitting Diode Chips. <i>ACS Applied Electronic Materials</i> , 2021, 3, 778-788.	4.3	41
5	Nonmechanical parfocal and autofocus features based on wave propagation distribution in lensfree holographic microscopy. <i>Scientific Reports</i> , 2021, 11, 3213.	3.3	5
6	Size-Dependent Electroluminescence and Current-Voltage Measurements of Blue InGaN/GaN μ LEDs down to the Submicron Scale. <i>Nanomaterials</i> , 2021, 11, 836.	4.1	11
7	A Compact Calibratable Pulse Oximeter Based on Color Filters: Towards a Quantitative Analysis of Measurement Uncertainty. <i>IEEE Sensors Journal</i> , 2021, 21, 7522-7531.	4.7	6
8	Wafer-scale transfer route for top-down III-nitride nanowire LED arrays based on the femtosecond laser lift-off technique. <i>Microsystems and Nanoengineering</i> , 2021, 7, 32.	7.0	27
9	A Novel Approach for a Chip-Sized Scanning Optical Microscope. <i>Micromachines</i> , 2021, 12, 527.	2.9	1
10	Pursuing the Diffraction Limit with Nano-LED Scanning Transmission Optical Microscopy. <i>Sensors</i> , 2021, 21, 3305.	3.8	4
11	Time-resolved cathodoluminescence investigations of AlN:Ge/GaN nanowire structures. <i>Nano Express</i> , 2021, 2, 034001.	2.4	3
12	Individually Switchable InGaN/GaN Nano-LED Arrays as Highly Resolved Illumination Engines. <i>Electronics (Switzerland)</i> , 2021, 10, 1829.	3.1	4
13	Processing and Characterization of Monolithic Passive-Matrix GaN-Based MicroLED Arrays With Pixel Sizes From 5 to 50 μ m. <i>IEEE Photonics Journal</i> , 2021, 13, 1-9.	2.0	5
14	Vertical 3D gallium nitride field-effect transistors based on fin structures with inverted p-doped channel. <i>Semiconductor Science and Technology</i> , 2021, 36, 014002.	2.0	13
15	Dynamic and Capacitive Characterization of 3D GaN n-p-n Vertical Fin-FETs. , 2021, , .		0
16	Femtosecond Laser Lift-Off with Sub-Bandgap Excitation for Production of Free-Standing GaN Light-Emitting Diode Chips. <i>Advanced Engineering Materials</i> , 2020, 22, 1901192.	3.5	28
17	Directly addressable GaN-based nano-LED arrays: fabrication and electro-optical characterization. <i>Microsystems and Nanoengineering</i> , 2020, 6, 88.	7.0	30
18	Toward three-dimensional hybrid inorganic/organic optoelectronics based on GaN/oCVD-PEDOT structures. <i>Nature Communications</i> , 2020, 11, 5092.	12.8	19

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19	Highly stable threshold voltage in GaN nanowire FETs: The advantages of i -GaN channel/ Al_2O_3 gate insulator. Applied Physics Letters, 2020, 117, .	3.3	15
20	Point Defect-Induced UV-C Absorption in Aluminum Nitride Epitaxial Layers Grown on Sapphire Substrates by Metal-Organic Chemical Vapor Deposition. Physica Status Solidi (B): Basic Research, 2020, 257, 2000278.	1.5	12
21	Visible Light-Driven p-Type Semiconductor Gas Sensors Based on $CaFe_2O_4$ Nanoparticles. Sensors, 2020, 20, 850.	3.8	16
22	Plasma profiling time-of-flight mass spectrometry for fast elemental analysis of semiconductor structures with depth resolution in the nanometer range. Semiconductor Science and Technology, 2020, 35, 035006.	2.0	0
23	Optical second- and third-harmonic generation on excitons in ZnSe/BeTe quantum wells. Physical Review B, 2020, 102, .	3.2	2
24	Nano illumination microscopy: a technique based on scanning with an array of individually addressable nanoLEDs. Optics Express, 2020, 28, 19044.	3.4	18
25	Instrumentation for Nano-Illumination Microscopy Based on InGaN/GaN NanoLED Arrays. , 2020, , .		0
26	UV-LED Photo-Activated Room Temperature NO_2 Sensors Based on Nanostructured ZnO/ AlN Thin Films. Proceedings (mdpi), 2019, 2, .	0.2	3
27	Top-down GaN nanowire transistors with nearly zero gate hysteresis for parallel vertical electronics. Scientific Reports, 2019, 9, 10301.	3.3	32
28	Facile and Efficient Atomic Hydrogenation Enabled Black TiO_2 with Enhanced Photo-Electrochemical Activity via a Favorably Low-Energy Barrier Pathway. Advanced Energy Materials, 2019, 9, 1900725.	19.5	21
29	Electroluminescence and current-voltage measurements of single-(In,Ga)N/GaN-nanowire light-emitting diodes in a nanowire ensemble. Beilstein Journal of Nanotechnology, 2019, 10, 1177-1187.	2.8	8
30	Piezoresistive Microcantilevers 3D-Patterned Using ZnO-Nanorods@Silicon-Nanopillars for Room-Temperature Ethanol Detection. , 2019, , .		3
31	Nano-structured transmissive spectral filter matrix based on guided-mode resonances. Journal of the European Optical Society-Rapid Publications, 2019, 15, .	1.9	6
32	Ultra Low Power Mass-Produced Gas Sensor Based on Efficient Self-Heated GaN Nanorods. , 2019, , .		2
33	A Light-Activated Micropower Gas Sensor for the Detection of NO_2 Down to the Parts Per Billion Range. , 2019, , .		0
34	A Microwatt Gas Sensor for NO_2 Detection in the Parts Per Billion Range. , 2019, , .		1
35	Efficient Self-Heating in Gallium Nitride Nanopillars for Ultra-Low-Power Mass-Produced Gas Sensors. , 2019, , .		0
36	Thermoelectric Generators Fabricated from Large-Scale-Produced Zr-/Hf-Based Half-Heusler Compounds Using Ag Sinter Bonding. Journal of Electronic Materials, 2019, 48, 5363-5374.	2.2	3

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37	Vertical GaN Nanowires and Nanoscale Light-Emitting-Diode Arrays for Lighting and Sensing Applications. ACS Applied Nano Materials, 2019, 2, 4133-4142.	5.0	44
38	Continuous Live-Cell Culture Imaging and Single-Cell Tracking by Computational Lensfree LED Microscopy. Sensors, 2019, 19, 1234.	3.8	16
39	Demonstration of UV-Induced Threshold Voltage Instabilities in Vertical GaN Nanowire Array-Based Transistors. IEEE Transactions on Electron Devices, 2019, 66, 2119-2124.	3.0	5
40	3D GaN nanoarchitecture for field-effect transistors. Micro and Nano Engineering, 2019, 3, 59-81.	2.9	32
41	Micro light plates for low-power photoactivated (gas) sensors. Applied Physics Letters, 2019, 114, .	3.3	42
42	A Parts Per Billion (ppb) Sensor for NO ₂ with Microwatt (1/4W) Power Requirements Based on Micro Light Plates. ACS Sensors, 2019, 4, 822-826.	7.8	85
43	Beyond solid-state lighting: Miniaturization, hybrid integration, and applications of GaN nano- and micro-LEDs. Applied Physics Reviews, 2019, 6, .	11.3	194
44	Silicon Nanopillars with ZNO Nanorods by Nanosphere Lithography on a Piezoresistive Microcantilever. , 2019, , .		2
45	Fabrication of SiO ₂ microcantilever arrays for mechanical loss measurements. Materials Research Express, 2019, 6, 045206.	1.6	1
46	3D GaN Fins as a Versatile Platform for a€Plane€Based Devices. Physica Status Solidi (B): Basic Research, 2019, 256, 1800477.	1.5	7
47	Electron beam lithography for contacting single nanowires on non-flat suspended substrates. Sensors and Actuators B: Chemical, 2019, 286, 616-623.	7.8	7
48	Method for non-invasive hemoglobin oxygen saturation measurement using broadband light source and color filters. , 2019, , .		2
49	Towards a super-resolution structured illumination microscope based on an array of nanoLEDs. , 2019, , .		2
50	Enhancement of the Sub-Band-Gap Photoconductivity in ZnO Nanowires through Surface Functionalization with Carbon Nanodots. Journal of Physical Chemistry C, 2018, 122, 1852-1859.	3.1	23
51	Performance analysis and simulation of vertical gallium nitride nanowire transistors. Solid-State Electronics, 2018, 144, 73-77.	1.4	13
52	Top-Down Fabrication of Arrays of Vertical GaN Nanorods with Freestanding Top Contacts for Environmental Exposure. Proceedings (mdpi), 2018, 2, .	0.2	1
53	Pixel-Wise Multispectral Sensing System Using Nanostructured Filter Matrix for Biomedical Applications. Proceedings (mdpi), 2018, 2, 880.	0.2	1
54	Structural Modifications in Free-Standing InGaN/GaN LEDs after Femtosecond Laser Lift-Off. Proceedings (mdpi), 2018, 2, .	0.2	3

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55	Artificial Neural Networks for Automated Cell Quantification in Lensless LED Imaging Systems. Proceedings (mdpi), 2018, 2, .	0.2	1
56	Visible Light Activated Room Temperature Gas Sensors Based on CaFe ₂ O ₄ Nanopowders. Proceedings (mdpi), 2018, 2, 834.	0.2	3
57	InGaN/GaN nanoLED Arrays as a Novel Illumination Source for Biomedical Imaging and Sensing Applications. Proceedings (mdpi), 2018, 2, .	0.2	8
58	Area-Selective Growth of Aligned ZnO Nanorod Arrays for MEMS Device Applications. Proceedings (mdpi), 2018, 2, .	0.2	11
59	Continuous Live-Cell Culture Monitoring by Compact Lensless LED Microscopes. Proceedings (mdpi), 2018, 2, .	0.2	3
60	Direct imaging of Indium-rich triangular nanoprisms self-organized formed at the edges of InGaN/GaN core-shell nanorods. Scientific Reports, 2018, 8, 16026.	3.3	19
61	Defect generation by nitrogen during pulsed sputter deposition of GaN. Journal of Applied Physics, 2018, 124, 175701.	2.5	6
62	Pinhole microLED Array as Point Source Illumination for Miniaturized Lensless Cell Monitoring Systems. Proceedings (mdpi), 2018, 2, .	0.2	3
63	Transferable Substrateless GaN LED Chips Produced by Femtosecond Laser Lift-Off for Flexible Sensor Applications. Proceedings (mdpi), 2018, 2, 891.	0.2	3
64	Thermal performance analysis of GaN nanowire and fin-shaped power transistors based on self-consistent electrothermal simulations. Microelectronics Reliability, 2018, 91, 227-231.	1.7	2
65	Nanofabrication of SOI-Based Photonic Waveguide Resonators for Gravimetric Molecule Detection. Proceedings (mdpi), 2018, 2, 1055.	0.2	0
66	Fabrication and characterization of single-pair thermoelectric generators of bismuth telluride using silver-sintering technology. Materials Today: Proceedings, 2018, 5, 10401-10407.	1.8	2
67	Traceable Nanomechanical Metrology of GaN Micropillar Array. Advanced Engineering Materials, 2018, 20, 1800353.	3.5	11
68	Zn acceptor position in GaN:Zn probed by contactless electroreflectance spectroscopy. Applied Physics Letters, 2018, 113, .	3.3	8
69	Normally Off Vertical 3-D GaN Nanowire MOSFETs With Inverted $\text{p}^+\text{-GaN}$ Channel. IEEE Transactions on Electron Devices, 2018, 65, 2439-2445.	3.0	32
70	Photoluminescence of planar and 3D InGaN/GaN LED structures excited with femtosecond laser pulses close to the damage threshold. Scientific Reports, 2018, 8, 11560.	3.3	11
71	GaN nanowire arrays with nonpolar sidewalls for vertically integrated field-effect transistors. Nanotechnology, 2017, 28, 095206.	2.6	58
72	The influence of MOVPE growth conditions on the shell of core-shell GaN microrod structures. Journal of Crystal Growth, 2017, 465, 34-42.	1.5	8

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73	Gold-modified indium tin oxide as a transparent window in optoelectronic diagnostics of electrochemically active biofilms. <i>Biosensors and Bioelectronics</i> , 2017, 94, 74-80.	10.1	24
74	Structure and Composition of Isolated Core-Shell $\text{In}_x\text{Ga}_{1-x}\text{N}$ Nanorods Based on Nanofocus X-Ray Diffraction and Scanning Transmission Electron Microscopy. <i>Physical Review</i>	3.8	12
75	Recombination dynamics in planar and three-dimensional InGaN/GaN light emitting diode structures. <i>Journal of Materials Research</i> , 2017, 32, 2456-2463.	2.6	4
76	Highly Specific and Wide Range NO_2 Sensor with Color Readout. <i>ACS Sensors</i> , 2017, 2, 1612-1618.	7.8	11
77	Photo-assisted Kelvin probe force microscopy investigation of three dimensional GaN structures with various crystal facets, doping types, and wavelengths of illumination. <i>Journal of Applied Physics</i> , 2017, 122, 085307.	2.5	9
78	Study of 3D-growth conditions for selective area MOVPE of high aspect ratio GaN fins with non-polar vertical sidewalls. <i>Journal of Crystal Growth</i> , 2017, 476, 90-98.	1.5	17
79	Enhanced Photoelectrochemical Behavior of H-TiO ₂ Nanorods Hydrogenated by Controlled and Local Rapid Thermal Annealing. <i>Nanoscale Research Letters</i> , 2017, 12, 336.	5.7	16
80	Anomalous surface potential behavior observed in InN by photoassisted Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2017, 110, 222103.	3.3	3
81	Nanofabrication of Vertically Aligned 3D GaN Nanowire Arrays with Sub-50 nm Feature Sizes Using Nanosphere Lift-off Lithography. <i>Proceedings (mdpi)</i> , 2017, 1, 309.	0.2	4
82	Vertical 3D GaN Nanoarchitectures towards an Integrated Optoelectronic Biosensing Platform in Microbial Fuel Cells. <i>Proceedings (mdpi)</i> , 2017, 1, .	0.2	1
83	LED-Based Tomographic Imaging for Live-Cell Monitoring of Pancreatic Islets in Microfluidic Channels. <i>Proceedings (mdpi)</i> , 2017, 1, .	0.2	7
84	Charge Transfer Characteristics of n-type $\text{In}_{0.1}\text{Ga}_{0.9}\text{N}$ Photoanode across Semiconductor-Liquid Interface. <i>Journal of Physical Chemistry C</i> , 2016, 120, 28917-28923.	3.1	2
85	Direct correlations of structural and optical properties of three-dimensional GaN/InGaN core/shell micro-light emitting diodes. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FJ09.	1.5	22
86	Effect of Potentiostatic and Galvanostatic Electrodeposition Modes on the Basic Parameters of Solar Cells Based on Cu_2O Thin Films. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, Q183-Q187.	1.8	23
87	Integrated Strategy toward Self-Powering and Selectivity Tuning of Semiconductor Gas Sensors. <i>ACS Sensors</i> , 2016, 1, 1256-1264.	7.8	28
88	Characterization of the internal properties of InGaN/GaN core-shell LEDs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 11-18.	1.8	12
89	Nanofocus x-ray diffraction and cathodoluminescence investigations into individual core-shell (In,Ga)N/GaN rod light-emitting diodes. <i>Nanotechnology</i> , 2016, 27, 325707.	2.6	18
90	Phosphor-converted white light from blue-emitting InGaN microrod LEDs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 1577-1584.	1.8	48

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91	Fabrication and characterization of low cost Cu ₂ O/ZnO:Al solar cells for sustainable photovoltaics with earth abundant materials. <i>Solar Energy Materials and Solar Cells</i> , 2016, 145, 454-461.	6.2	40
92	High Aspect Ratio GaN Fin Microstructures with Nonpolar Sidewalls by Continuous Mode Metalorganic Vapor Phase Epitaxy. <i>Crystal Growth and Design</i> , 2016, 16, 1458-1462.	3.0	30
93	Insights into Interfacial Changes and Photoelectrochemical Stability of In _x Ga _{1-x} N (0001) Photoanode Surfaces in Liquid Environments. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 8232-8238.	8.0	23
94	Growth mechanisms of GaN microrods for 3D core-shell LEDs: The influence of silane flow. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 2830-2836.	1.8	34
95	Surface photovoltage behavior of GaN columns. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 732-735.	1.8	5
96	Growth and characterization of mixed polar GaN columns and core-shell LEDs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 727-731.	1.8	9
97	Investigation of Thermoelectric Parameters of Bi ₂ Te ₃ : TEGs Assembled using Pressure-Assisted Silver Powder Sintering-Based Joining Technology. <i>Journal of Electronic Materials</i> , 2015, 44, 2055-2060.	2.2	7
98	Electrothermal piezoresistive cantilever resonators for personal measurements of nanoparticles in workplace exposure. <i>Proceedings of SPIE</i> , 2015, , .	0.8	3
99	Handheld personal airborne nanoparticle detector based on microelectromechanical silicon resonant cantilever. <i>Microelectronic Engineering</i> , 2015, 145, 96-103.	2.4	59
100	Fabrication of wear-resistant silicon microprobe tips for high-speed surface roughness scanning devices. <i>Proceedings of SPIE</i> , 2015, , .	0.8	2
101	Demonstration of (In, Ga)N/GaN Core-shell Micro Light-Emitting Diodes Grown by Molecular Beam Epitaxy on Ordered MOVPE GaN Pillars. <i>Crystal Growth and Design</i> , 2015, 15, 3661-3665.	3.0	17
102	Fabrication and characterization of flexible solar cell from electrodeposited Cu ₂ O thin film on plastic substrate. <i>Solar Energy</i> , 2015, 122, 1193-1198.	6.1	41
103	Vertical silicon nanowire array-patterned microcantilever resonators for enhanced detection of cigarette smoke aerosols. <i>Micro and Nano Letters</i> , 2014, 9, 676-679.	1.3	26
104	Growth kinetics and mass transport mechanisms of GaN columns by selective area metal organic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	44
105	Oxides for sustainable photovoltaics with earth-abundant materials. <i>Proceedings of SPIE</i> , 2014, , .	0.8	5
106	Highly Selective SAM-Nanowire Hybrid NO ₂ Sensor: Insight into Charge Transfer Dynamics and Alignment of Frontier Molecular Orbitals. <i>Advanced Functional Materials</i> , 2014, 24, 595-602.	14.9	71
107	Finite element modeling and experimental proof of NEMS-based silicon pillar resonators for nanoparticle mass sensing applications. <i>Microsystem Technologies</i> , 2014, 20, 571-584.	2.0	31
108	A phase-locked loop frequency tracking system for portable microelectromechanical piezoresistive cantilever mass sensors. <i>Microsystem Technologies</i> , 2014, 20, 559-569.	2.0	44

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109	A Highly Selective and Self-Powered Gas Sensor Via Organic Surface Functionalization of p-Si/n-ZnO Diodes. <i>Advanced Materials</i> , 2014, 26, 8017-8022.	21.0	103
110	Characterisation of 3D GaN/InGaN core-shell nanostructures by transmission electron microscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 425-427.	0.8	9
111	In-plane-excited silicon nanowire arrays-patterned cantilever sensors for enhanced airborne particulate matter exposure detection. , 2014, , .		0
112	Thermoelectric Coolers with Sintered Silver Interconnects. <i>Journal of Electronic Materials</i> , 2014, 43, 2397-2404.	2.2	15
113	Band Engineered Epitaxial 3D GaN-InGaN Core-Shell Rod Arrays as an Advanced Photoanode for Visible-Light-Driven Water Splitting. <i>ACS Applied Materials & Interfaces</i> , 2014, 6, 2235-2240.	8.0	69
114	Continuous-Flow MOVPE of Ga-Polar GaN Column Arrays and Core-Shell LED Structures. <i>Crystal Growth and Design</i> , 2013, 13, 3475-3480.	3.0	80
115	High-Temperature Performance of Stacked Silicon Nanowires for Thermoelectric Power Generation. <i>Journal of Electronic Materials</i> , 2013, 42, 2233-2238.	2.2	19
116	The MOVPE growth mechanism of catalyst-free self-organized GaN columns in H ₂ and N ₂ carrier gases. <i>Journal of Crystal Growth</i> , 2013, 384, 61-65.	1.5	6
117	Determination of zinc concentration in GaN:Zn,Si from photoluminescence. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 523-526.	0.8	4
118	Group III nitride core-shell nano-rod and microrods for optoelectronic applications. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013, 7, 800-814.	2.4	76
119	Silicon Nanowire Resonators: Aerosol Nanoparticle Mass Sensing in the Workplace. <i>IEEE Nanotechnology Magazine</i> , 2013, 7, 18-23.	1.3	18
120	Silicon nanowire resonators for aerosol nanoparticle mass sensing. , 2013, , .		0
121	Silicon resonant nanopillar sensors for airborne titanium dioxide engineered nanoparticle mass detection. <i>Sensors and Actuators B: Chemical</i> , 2013, 189, 146-156.	7.8	63
122	Portable cantilever-based airborne nanoparticle detector. <i>Sensors and Actuators B: Chemical</i> , 2013, 187, 118-127.	7.8	50
123	Airborne engineered nanoparticle mass sensor based on a silicon resonant cantilever. <i>Sensors and Actuators B: Chemical</i> , 2013, 180, 77-89.	7.8	136
124	Evaluation of photoresist-based nanoparticle removal method for recycling silicon cantilever mass sensors. <i>Sensors and Actuators A: Physical</i> , 2013, 202, 90-99.	4.1	30
125	Mechanism of nucleation and growth of catalyst-free self-organized GaN columns by MOVPE. <i>Journal Physics D: Applied Physics</i> , 2013, 46, 205101.	2.8	11
126	Simulation and characterization of silicon nanopillar-based nanoparticle sensors. , 2013, , .		1

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127	Toward Three-Dimensional Microelectronic Systems: Directed Self-Assembly of Silicon Microcubes via DNA Surface Functionalization. Langmuir, 2013, 29, 8410-8416.	3.5	8
128	Dependence of N-polar GaN rod morphology on growth parameters during selective area growth by MOVPE. Journal of Crystal Growth, 2013, 364, 149-154.	1.5	23
129	Femtogram aerosol nanoparticle mass sensing utilising vertical silicon nanowire resonators. Micro and Nano Letters, 2013, 8, 554-558.	1.3	38
130	MEMS-based silicon cantilevers with integrated electrothermal heaters for airborne ultrafine particle sensing. Proceedings of SPIE, 2013, , .	0.8	4
131	A closed-loop system for frequency tracking of piezoresistive cantilever sensors. , 2013, , .		0
132	Vapour phase epitaxy of Cu ₂ O on a-plane Al ₂ O ₃ . Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1284-1287.	0.8	4
133	Fabrication of vertical nanowire resonators for aerosol exposure assessment. Proceedings of SPIE, 2013, , .	0.8	0
134	GaN BASED 3D CORE-SHELL LEDs. International Journal of High Speed Electronics and Systems, 2012, 21, 1250008.	0.7	2
135	Packaging of MEMS and MOEMS for harsh environments. Journal of Micro/ Nanolithography, MEMS, and MOEMS, 2012, 11, 021202-1.	0.9	6
136	Sinter-attach of high-temperature sensors for deep-drilling monitoring. , 2012, , .		1
137	GaN based nanorods for solid state lighting. Journal of Applied Physics, 2012, 111, .	2.5	463
138	Polarity Control in 3D GaN Structures Grown by Selective Area MOVPE. Crystal Growth and Design, 2012, 12, 2552-2556.	3.0	45
139	Effect of Photoresist Coating on the Reusable Resonant Cantilever Sensors for Assessing Exposure to Airborne Nanoparticles. Procedia Engineering, 2012, 47, 302-305.	1.2	1
140	Femtogram Mass Measurement of Airborne Engineered Nanoparticles using Silicon Nanopillar Resonators. Procedia Engineering, 2012, 47, 289-292.	1.2	5
141	Sintering of Copper Particles for Die Attach. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2012, 2, 1587-1591.	2.5	60
142	Luminescence and efficiency optimization of InGaN/GaN core-shell nanowire LEDs by numerical modelling. Proceedings of SPIE, 2012, , .	0.8	12
143	Nitrogen-polar core-shell GaN light-emitting diodes grown by selective area metalorganic vapor phase epitaxy. Applied Physics Letters, 2012, 101, .	3.3	29
144	Transparent conductive Ga-doped ZnO films fabricated by MOCVD. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 708-713.	1.8	13

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145	Zn doped GaN for single-photon emission. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1024-1027.	0.8	2
146	Two step deposition method with a high growth rate for ZnO nanowire arrays and its application in photovoltaics. Thin Solid Films, 2012, 520, 4637-4641.	1.8	10
147	Fabrication and characterization of nanoporous ZnO layers for sensing applications. Thin Solid Films, 2012, 520, 4662-4665.	1.8	11
148	Pick-and-Place Silver Sintering Die Attach of Small-Area Chips. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2012, 2, 199-207.	2.5	42
149	Analysis and Modeling of Thermomechanically Improved Silver-Sintered Die-Attach Layers Modified by Additives. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2011, 1, 1846-1855.	2.5	30
150	Computational study of carrier injection in III-nitride core-shell nanowire-LEDs. , 2011, , .		4
151	Interpretation of transport measurements in ZnO-thin films. Applied Physics A: Materials Science and Processing, 2011, 102, 161-168.	2.3	3
152	Towards nanorod LEDs: Numerical predictions and controlled growth. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2305-2307.	0.8	8
153	Polarity analysis of GaN nanorods by photo-assisted Kelvin probe force microscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2157-2159.	0.8	21
154	The nanorod approach: GaN NanoLEDs for solid state lighting. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2296-2301.	0.8	128
155	Selective area growth of GaN rod structures by MOVPE: Dependence on growth conditions. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2318-2320.	0.8	10
156	Implementation of ZnO/ZnMgO strained-layer superlattice for ZnO heteroepitaxial growth on sapphire. Journal of Crystal Growth, 2011, 323, 111-113.	1.5	6
157	Thermal characterization of vertical silicon nanowires. Journal of Materials Research, 2011, 26, 1958-1962.	2.6	17
158	Design and fabrication of piezoresistive p-SOI Wheatstone bridges for high-temperature applications. , 2011, , .		3
159	ZnO-GaN Hybrid Heterostructures as Potential Cost-Efficient LED Technology. Proceedings of the IEEE, 2010, 98, 1281-1287.	21.3	25
160	GaN and LED structures grown on pre-patterned silicon pillar arrays. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 84-87.	0.8	11
161	GaN nanorods and LED structures grown on patterned Si and AlN/Si substrates by selective area growth. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2224-2226.	0.8	14
162	Die-attach for high-temperature applications using fineplacer-pressure-sintering (FPS). , 2010, , .		8

#	ARTICLE	IF	CITATIONS
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